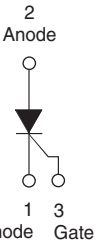
Surface Mountable Phase Control SCR, 16 A

D²PAK



FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compliant to RoHS directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition
- Designed and qualified for industrial level

Pb
e3
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-16TTS..SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRODUCT SUMMARY	
V_T at 10 A	< 1.4 V
I_{TSM}	200 A
V_{RRM}	800 V/1200 V

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5	A
Aluminum IMS, R_{thCA} = 15 °C/W	6.3	9.5	
Aluminum IMS with heatsink, R_{thCA} = 5 °C/W	14.0	18.5	

Note

- T_A = 55 °C, T_J = 125 °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	10	A
I_{RMS}		16	
V_{RRM}/V_{DRM}		800/1200	V
I_{TSM}		200	A
V_T	10 A, T_J = 25 °C	1.4	V
dV/dt		500	V/µs
dI/dt		150	A/µs
T_J		- 40 to 125	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM}, MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM}, MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-16TTS08SPbF	800	800	10
VS-16TTS12SPbF	1200	1200	

For technical questions within your region, please contact one of the following:
DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES TYP.	VALUES MAX.	UNITS
Maximum average on-state current	$I_{T(AV)}$	T_C = 98 °C, 180° conduction, half sine wave	10		A
Maximum RMS on-state current	I_{RMS}		16		
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	170		
		10 ms sine pulse, no voltage reapplied	200		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	144		A^2s
		10 ms sine pulse, no voltage reapplied	200		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied	2000		$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	10 A, T_J = 25 °C	1.4		V
On-state slope resistance	r_t	T_J = 125 °C	24.0		mΩ
Threshold voltage	$V_{T(TO)}$		1.1		V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	T_J = 25 °C, V_R = Rated V_{RRM}/V_{DRM}	0.5		mA
		T_J = 125 °C, V_R = Rated V_{RRM}/V_{DRM}	10		
Holding current	I_H	Anode supply = 6 V, resistive load, initial I_T = 1 A	-	100	
Maximum latching current	I_L	Anode supply = 6 V, resistive load	200		
Maximum rate of rise of off-state voltage	dV/dt		500		V/µs
Maximum rate of rise of turned-on current	dI/dt		150		A/µs

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	+ I_{GM}		1.5	A
Maximum peak negative gate voltage	- V_{GM}		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	90	mA
		Anode supply = 6 V, resistive load, T_J = 25 °C	60	
		Anode supply = 6 V, resistive load, T_J = 125 °C	35	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	3.0	V
		Anode supply = 6 V, resistive load, T_J = 25 °C	2.0	
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	
Maximum DC gate voltage not to trigger	V_{GD}	T_J = 125 °C, V_{DRM} = Rated value	0.25	
Maximum DC gate current not to trigger	I_{GD}		2.0	mA

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	T_J = 25 °C	0.9	µs
Typical reverse recovery time	t_{rr}	T_J = 125 °C	4	
Typical turn-off time	t_q		110	

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Maximum junction and storage temperature range	T_J, T_{Stg}		- 40 to 125	°C
Soldering temperature	T_S	For 10 s (1.6 mm from case)	240	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.3	°C/W
Typical thermal resistance, junction to ambient	R_{thJA}	PCB mount (1)	40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D^2PAK (SMD-220)	16TTS08S	
			16TTS12S	

Note

(1) When mounted on 1" square (650 mm^2) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W.
For recommended footprint and soldering techniques refer to application note #AN-994.

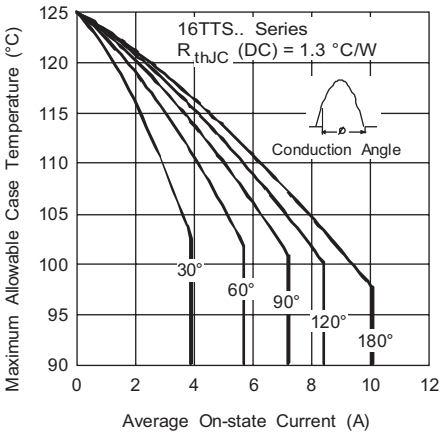


Fig. 1 - Current Rating Characteristics

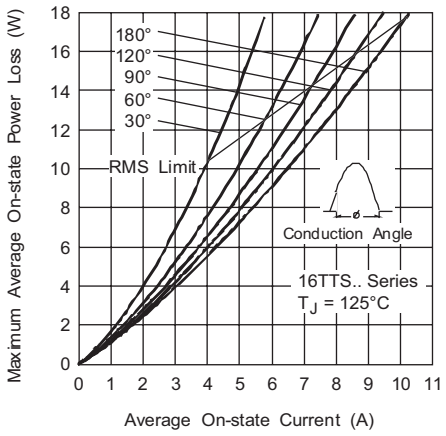


Fig. 3 - On-State Power Loss Characteristics

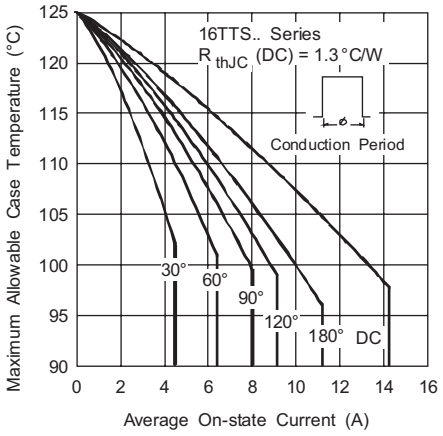


Fig. 2 - Current Rating Characteristics

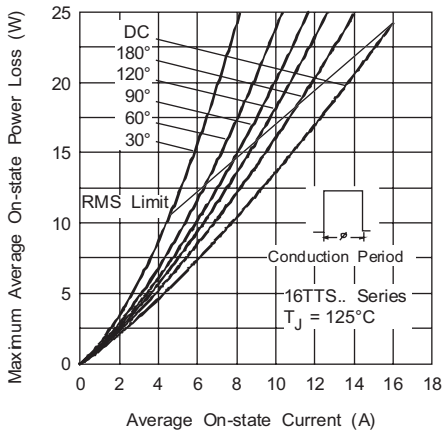


Fig. 4 - On-State Power Loss Characteristics

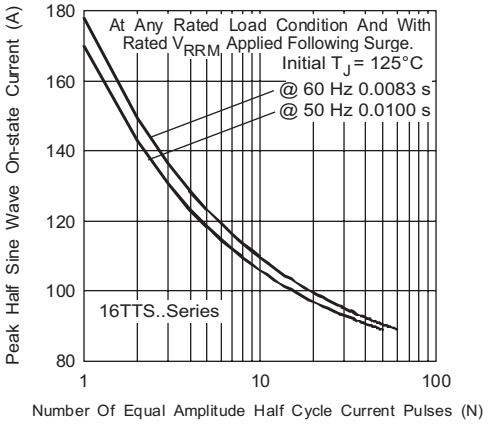


Fig. 5 - Maximum Non-Repetitive Surge Current

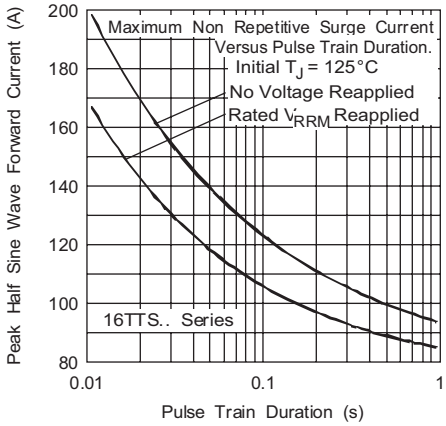


Fig. 6 - Maximum Non-Repetitive Surge Current

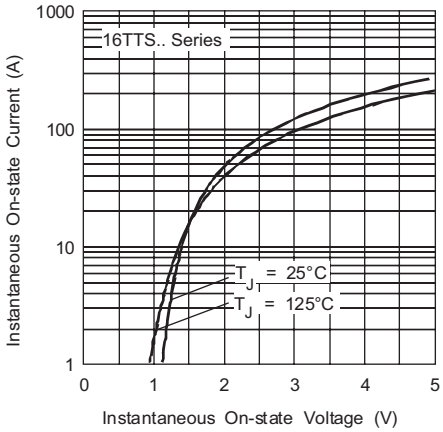


Fig. 7 - On-State Voltage Drop Characteristics

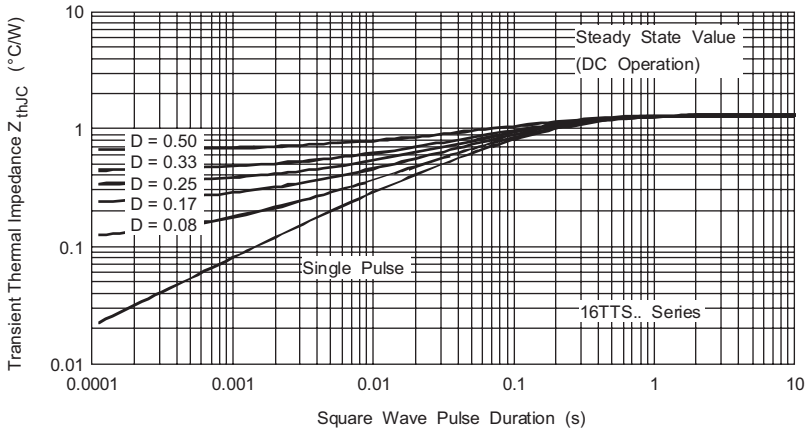


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

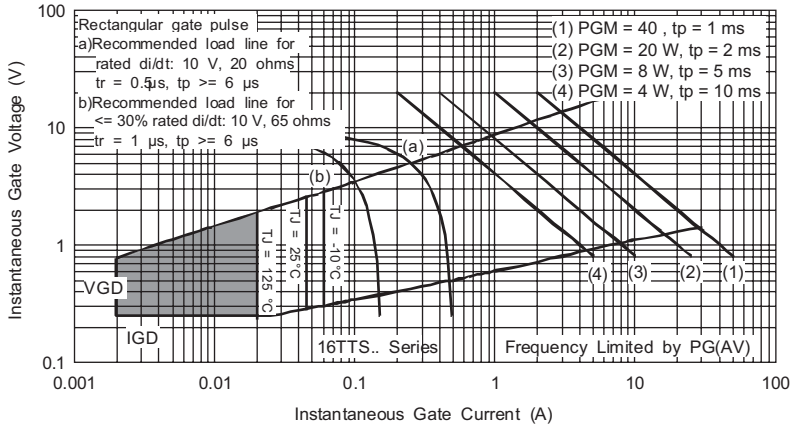


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

VS-	16	T	T	S	12	S	TRL	PbF
1	2	3	4	5	6	7	8	9

- **1** - HPP product suffix
- **2** - Current rating
- **3** - Circuit configuration:
  T = Single thyristor
- **4** - Package:
  T = TO-220AC
- **5** - Type of silicon:
  S = Standard recovery rectifier
- **6** - Voltage rating: Voltage code x 100 = V_{RRM} (08 = 800 V, 12 = 1200 V)
- **7** - S = TO-220 D^2PAK (SMD-220) version
- **8** - • None = Tube
  • TRL = Tape and reel (left oriented)
  • TRR = Tape and reel (right oriented)
- **9** - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95046
Part marking information	www.vishay.com/doc?95054
Packaging information	www.vishay.com/doc?95032

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